In the claims:

Please amend the claims as follows:

Claim 1 (currently amended): A method for manufacturing a semiconductor device having at least one thin film ~~transistors~~ transistor, said method comprising the steps of:

forming a semiconductor layer over a substrate;

irradiating said semiconductor layer with a laser beam to crystallize said semiconductor layer; and

forming source, drain and channel region of said thin film transistor within said semiconductor layer,

wherein said laser beam is a second harmonic component generated from a ~~continuous-oscillate~~ continuously-oscillating light source,

wherein the irradiation of said semiconductor layer is conducted in such a manner that said semiconductor layer is scanned with said laser beam in parallel with a carrier flow direction in said channel region.

Claim 2 (currently amended): A method for manufacturing a semiconductor device having at least one thin film ~~transistors~~ transistor, said method comprising the steps of:

forming a semiconductor layer over a substrate;

irradiating said semiconductor layer with a linear laser beam to crystallize said semiconductor layer; and

forming source, drain and channel region of said thin film transistor within said semiconductor layer,

wherein said linear laser beam is a second harmonic component generated from a ~~continuous-oscillate~~ continuously-oscillating light source,

wherein the irradiation of said semiconductor layer is conducted in such a manner that said semiconductor layer is scanned with said linear laser beam in parallel with a carrier flow direction in said channel region.

Claims 3-8 (withdrawn).

Claim 9 (currently amended): A method of manufacturing a semiconductor device having at least one thin film transistor, said method comprising the steps of:

forming a semiconductor layer over a substrate; and

irradiating said semiconductor layer with a linear laser beam to crystallize said semiconductor layer, while moving said substrate in a direction approximately perpendicular to a lengthy direction of said linear laser beam,

wherein said linear laser beam is a second harmonic component generated from a ~~continuous-oscillate~~ continuously-oscillating light source.

D1 cont.

Claim 10 (currently amended): A method of manufacturing a semiconductor device having at least one thin film transistor, said method comprising the steps of:

forming a semiconductor layer over a substrate;

irradiating said semiconductor layer with a laser beam to crystallize said semiconductor layer; and

patterning the crystallized semiconductor layer to form an active layer of said thin film transistor,

wherein said laser beam is a second harmonic component generated from a ~~continuous-oscillate~~ continuously-oscillating light source.

Claims 11-16 (withdrawn).

Claim 17 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein said semiconductor layer comprises amorphous silicon.

Claim 18 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein said semiconductor layer comprises silicon and germanium.

Claim 19 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains carbon at a concentration not higher than $5x10^{18}$atoms/cm^3.

D' Cancl'd

Claim 20 (previously amended): A method according to any one of claims 1, 2, 9 and 10, wherein the crystallized semiconductor layer contains oxygen at a concentration not higher than $5x10^{19}$atoms/cm^3.

Claim 21-30 (withdrawn).